

XPT IGBT

tentative

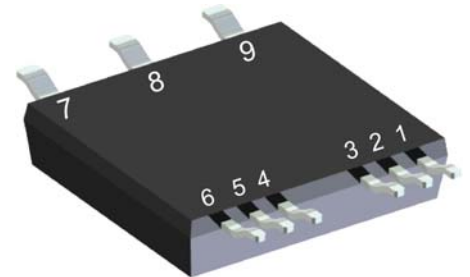
$$V_{CES} = 1200V$$

$$I_{C25} = 43A$$

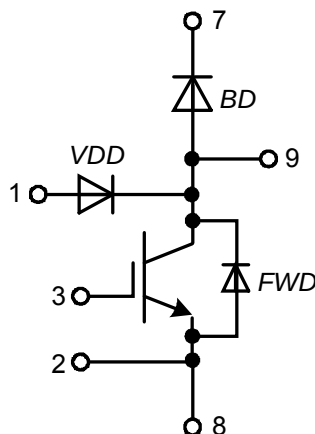
$$V_{CE(sat)} = 1.8V$$

ISOPLUS™ Surface Mount Power Device
Boost Topology
XPT IGBT

Part number

IXA30RG1200DHGLB


Backside: isolated

Features / Advantages:

- XPT IGBT
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance in resonant circuits
- Sonic™ diode
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
 - low temperature dependency of reverse recovery
- Vcesat detection diode (VDD)
 - integrated into package
 - very fast diode

Applications:

- AC drives
 - brake chopper
- PFC
 - boost chopper
- Switched reluctance drives

Package: SMPD

- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling
- Isolation Voltage: 3000 V~

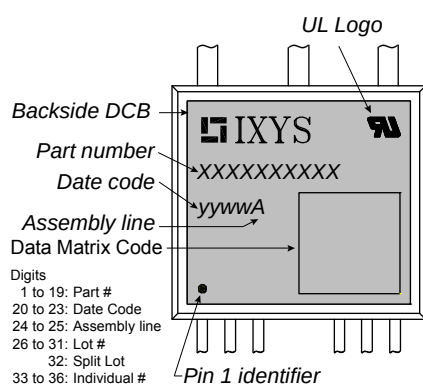
Free Wheeling Diode FWD				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V
I _R	reverse current, drain current	V _R = 1200 V	T _{VJ} = 25°C			30	μA
		V _R = 1200 V	T _{VJ} = 125°C			0.5	mA
V _F	forward voltage drop	I _F = 30 A	T _{VJ} = 25°C			2.20	V
		I _F = 60 A					V
		I _F = 30 A	T _{VJ} = 125°C			2.20	V
		I _F = 60 A					V
I _{FAV}	average forward current	T _C = 80°C	T _{VJ} = 150°C			25	A
		rectangular d = 0.5					
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 150°C		1.26	V
r _F	slope resistance					28	mΩ
R _{thJC}	thermal resistance junction to case					1	K/W
R _{thCH}	thermal resistance case to heatsink				0.30		K/W
P _{tot}	total power dissipation		T _C = 25°C			125	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V	T _{VJ} = 45°C			200	A
C _J	junction capacitance	V _R = 400 V f = 1 MHz	T _{VJ} = 25°C		13		pF

VCEsat Detection Diode VDD				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V
I _R	reverse current, drain current	V _{R/D} = 1200 V	T _{VJ} = 25°C			2	μA
		V _{R/D} = 1200 V	T _{VJ} = 125°C			0.03	mA
V _F	forward voltage drop	I _F = 1 A	T _{VJ} = 25°C			2.20	V
		I _F = 1 A	T _{VJ} = 125°C			1.80	V
V _{F0}	threshold voltage	} for power loss calculation only				1.30	V
r _F	slope resistance					390	mΩ
C _J	junction capacitance	V _R = 400 V; f = 1 MHz		T _{VJ} = 25°C		tbd	pF
I _{RM}	max. reverse recovery current	} V _R = 100 V; I _F = 1 A -di/dt = 100 A/μs		T _{VJ} = 25°C		2.3	A
t _{rr}	reverse recovery time			T _{VJ} = 125°C		tbd	A
				T _{VJ} = 25°C		40	ns
				T _{VJ} = 125°C		tbd	ns

Boost IGBT				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
V_{GES}	max. DC gate voltage					± 20	V
V_{GEM}	max. transient collector gate voltage					± 30	V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$				43	A
I_{C80}		$T_C = 80^{\circ}\text{C}$				30	A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				147	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 25\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		1.8	2.1	V
			$T_{VJ} = 125^{\circ}\text{C}$		2.1		V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 1\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	5.4	5.9	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			0.1	mA
			$T_{VJ} = 125^{\circ}\text{C}$		0.1		mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$				500	nA
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 25\text{ A}$			76		nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 25\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 39\text{ }\Omega$	$T_{VJ} = 125^{\circ}\text{C}$		70		ns
t_r	current rise time				40		ns
$t_{d(off)}$	turn-off delay time				250		ns
t_f	current fall time				100		ns
E_{on}	turn-on energy per pulse				2.5		mJ
E_{off}	turn-off energy per pulse				3		mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 39\text{ }\Omega$	$T_{VJ} = 125^{\circ}\text{C}$				
I_{CM}		$V_{CEmax} = 1200\text{ V}$				75	A
SCSOA	short circuit safe operating area	$V_{CEmax} = 1200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$				
t_{SC}	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V}$				10	μs
I_{SC}	short circuit current	$R_G = 39\text{ }\Omega$; non-repetitive			100		A
R_{thJC}	thermal resistance junction to case					0.85	K/W
R_{thCH}	thermal resistance case to heatsink				0.25		K/W
Boost Diode BD							
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}\text{C}$			1200	V
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			48	A
I_{F80}			$T_C = 80^{\circ}\text{C}$			32	A
V_F	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2.20	V
			$T_{VJ} = 125^{\circ}\text{C}$		1.90		V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$			0.03	mA
			$T_{VJ} = 125^{\circ}\text{C}$		0.15		mA
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $-di_F/dt = 600\text{ A}/\mu\text{s}$ $I_F = 30\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$		3.5		μC
I_{RM}	max. reverse recovery current				30		A
t_{rr}	reverse recovery time				350		ns
E_{rec}	reverse recovery energy				0.9		mJ
R_{thJC}	thermal resistance junction to case					1	K/W
R_{thCH}	thermal resistance case to heatsink				0.3		K/W

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Package SMPD		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal			100	A
T _{stg}	storage temperature		-55		150	°C
T _{VJ}	virtual junction temperature		-55		150	°C
Weight				8.5		g
F _C	mounting force with clip		40		130	N
V _{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute				2500
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	1.6			mm
d _{Spb/Apb}		terminal to backside				4.0



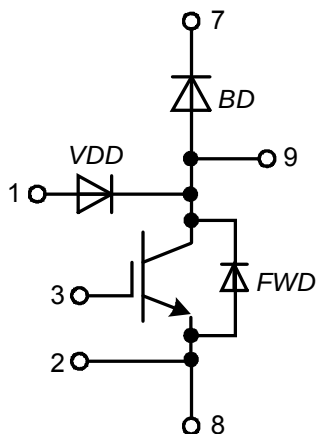
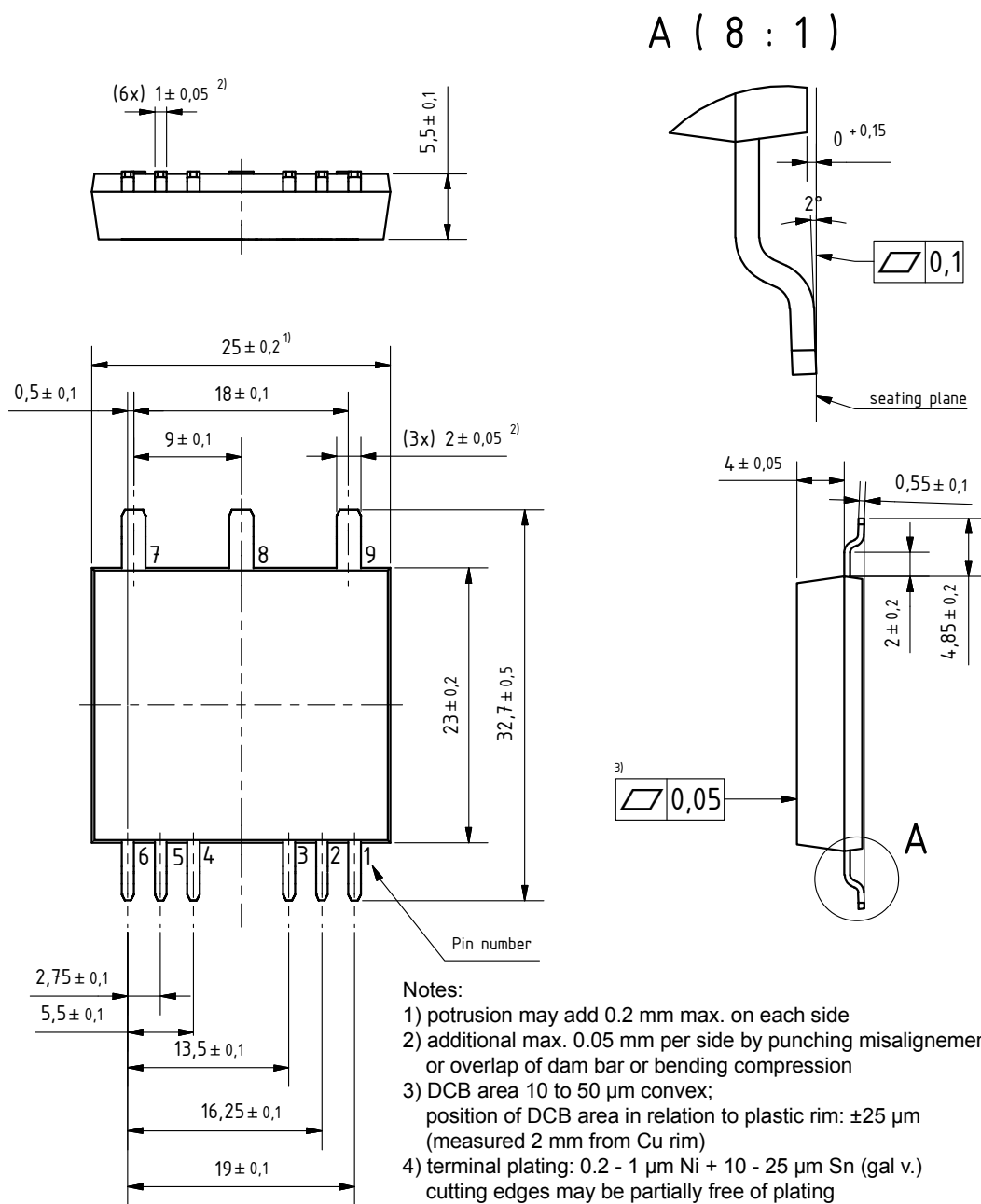
Part number

I = IGBT
 X = XPT IGBT
 A = Gen 1 / std
 30 = Current Rating [A]
 RG = boost configuration
 1200 = Reverse Voltage [V]
 D = IGBT
 H = XPT IGBT
 G = Gen 1 / std
 LB = SMPD-B

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA30RG1200DHGLB	IXA30RG1200DHGLB	Blister	45	512356
Alternative	IXA30RG1200DHGLB-TRR	IXA30RG1200DHGLB	Tape & Reel	200	511654

Similar Part	Package	Voltage class
IXA20RG1200DHGLB	SMPD-B	1200
IXA40RG1200DHGLB	SMPD-B	1200

Outlines SMPD



Boost IGBT

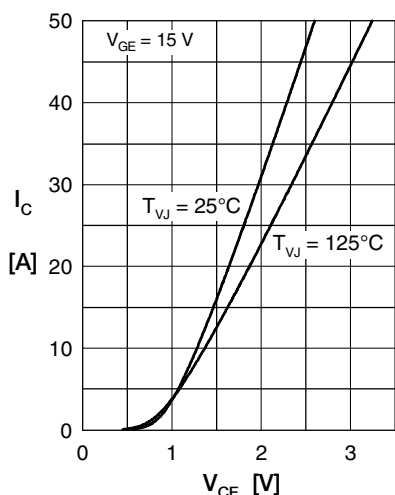


Fig. 1 Typ. output characteristics

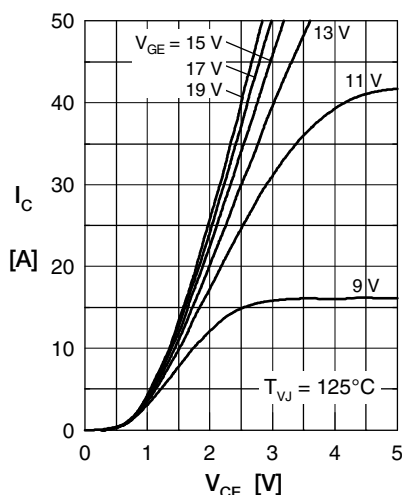


Fig. 2 Typ. output characteristics

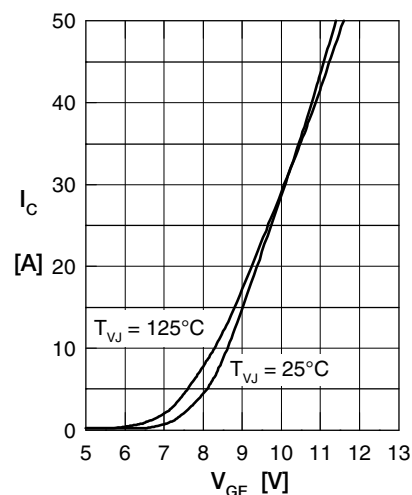


Fig. 3 Typ. transfer characteristics

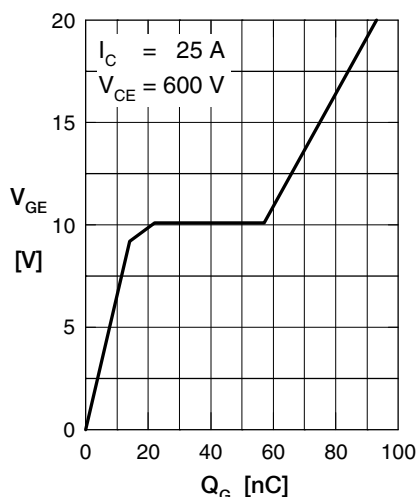


Fig. 4 Typ. turn-on gate charge

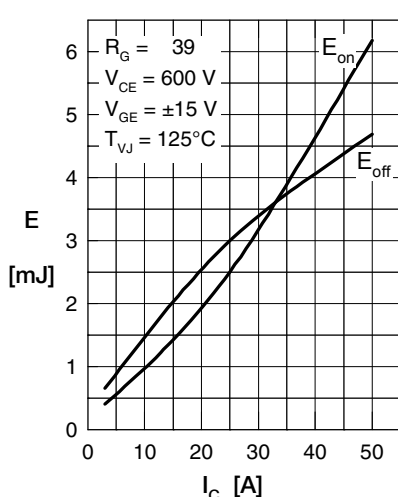


Fig. 5 Typ. switching energy versus collector current

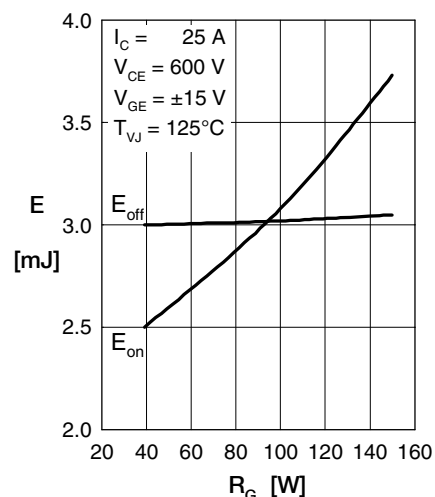


Fig. 6 Typ. switching energy versus gate resistance

Fig. 7 Typ. transient thermal impedance junction to case

Boost Diode BD

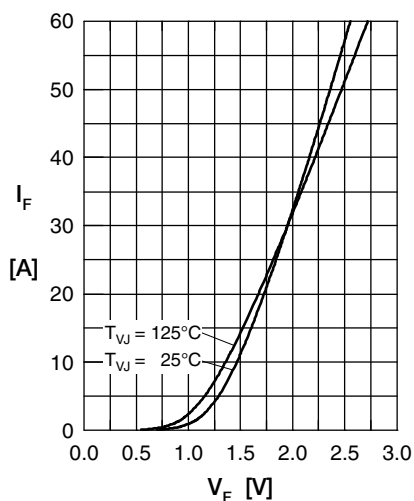


Fig. 1 Typ. Forward current versus V_F

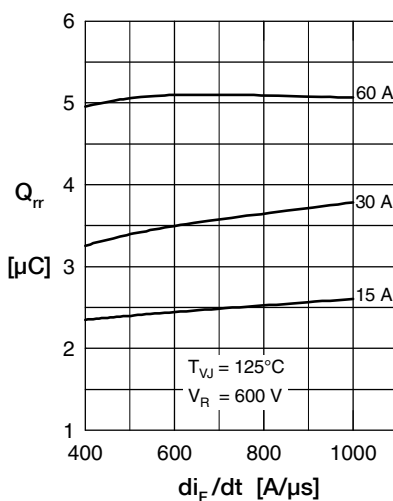


Fig. 2 Typ. reverse recov.charge Q_{rr} versus di/dt

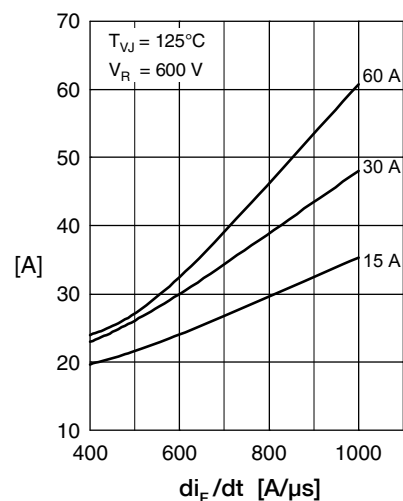


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

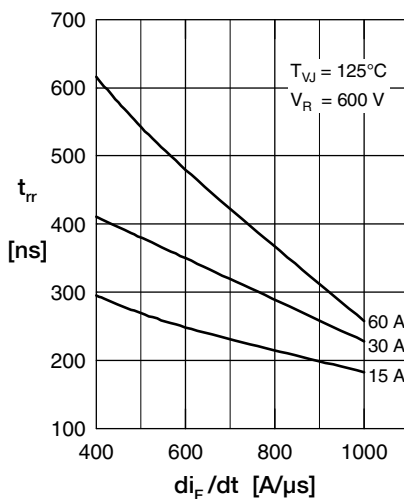


Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus di/dt

Fig. 5 Typ. recovery time t_{rr} versus di/dt

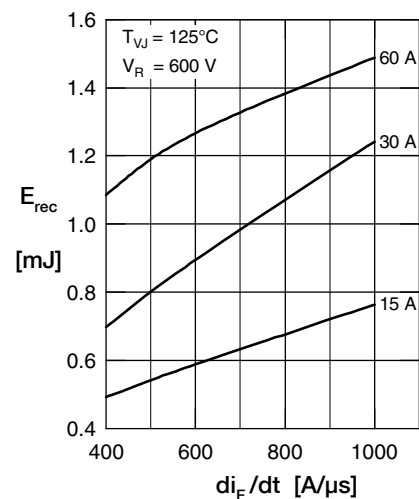


Fig. 6 Typ. recovery energy E_{rec} versus di/dt

Fig. 7 Typ. transient thermal impedance junction to case



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